

N-channel 80 V 8.7 m Ω standard level MOSFET in D2PAK

Rev. 2 — 2 March 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in D2PAK package gualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	-	-	90	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	170	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	14	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 13</u>	-	7.5	8.7	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 25 A; V_{DS} = 40 V;	-	11	-	nC
Q _{G(tot)}	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	52	-	nC
Avalanch	e ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_\text{D} = 90 \text{ A}; \\ V_{sup} \leq 80 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped} $	-	-	120	mJ

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN8R7-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

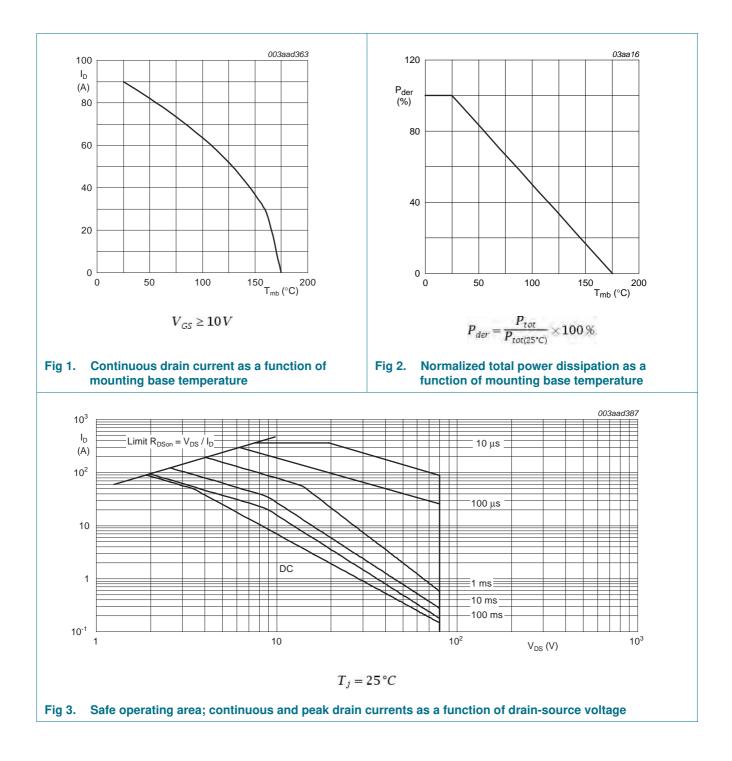
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	64	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	90	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	361	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	170	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	90	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	361	А
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ I}_{D} = 90 \text{ A};$ $V_{sup} \le 80 \text{ V}; \text{ R}_{GS} = 50 \Omega; \text{ unclamped}$	-	120	mJ

PSMN8R7-80BS

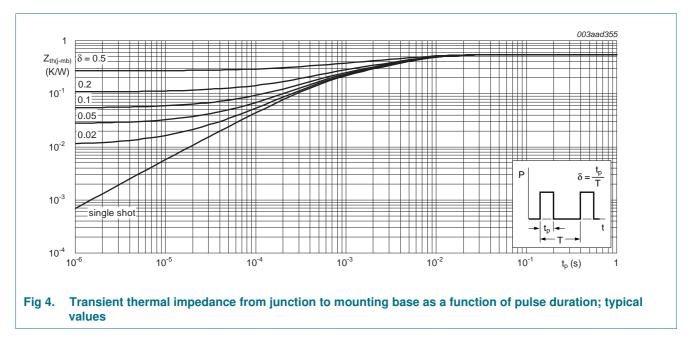
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.54	0.88	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	73	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 10	2.3	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.3	5	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; see <u>Figure 12</u>	-	-	20.88	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 100 °C; see Figure 12	-	-	14	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 13</u>	-	7.5	8.7	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	44	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	52	-	nC
Q _{GS}	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	15	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	9.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5.8	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 15}{100000000000000000000000000000000000$	-	4.6	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3346	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	296	-	pF
C _{rss}	reverse transfer capacitance		-	158	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 1.6 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	21	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	26	-	ns
t _{d(off)}	turn-off delay time		-	46	-	ns
t _f	fall time		-	20	-	ns

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Product data sheet

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Symbol

Source-drain diode

PSMN8R7-80BS

Typ

Max

Unit

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Min

V_{SD} source-drain voltage $I_{S} = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_{i} = 25 \text{ °C};$ 0.79 1.2 ٧ see Figure 17 $I_S = 25 \text{ A}; dI_S/dt = 100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ reverse recovery time 42 t_{rr} _ ns $V_{DS} = 40 V$ Qr recovered charge 66 nC --003aad449 003aad451 100 100 20 5.5 I_D I_D (A) 5 (A) 8 80 80 60 60 40 40 4.5 T_j = 175 °C 20 20 T_j = 25 °C $V_{GS}(V) = 4$ 0 0 0 1 2 ³ V_{DS} (V) ⁴ 0 2 4 6 V_{GS} (V) $T_i = 25 \,^{\circ}C$ $V_{DS} > I_D \times R_{DSom}$ Output characteristics: drain current as a Transfer characteristics: drain current as a Fig 5. Fig 6. function of drain-source voltage; typical values function of gate-source voltage; typical values 003aad455 003aad456 5000 100 С g_{fs} Ciss (pF) (S) 4000 80 Crss 3000 60 2000 40 1000 20 0 0 9 _{VGS (V)} 12 0 3 6 0 20 40 60 80 100 I_D (A) $V_{DS} = 0V; f = 1MHz$ $T_j = 25 \,^{\circ}C; V_{DS} = 15V$ Input and reverse transfer capacitances as a Fig 8. Forward transconductance as a function of Fig 7. function of gate-source voltage; typical values drain current; typical values

Table 6. Characteristics ... continued

Parameter

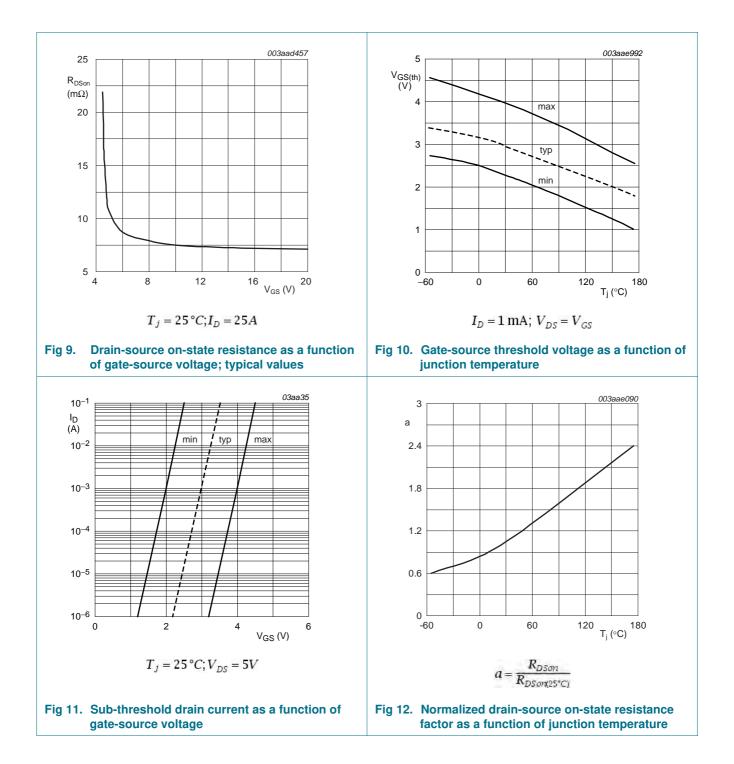
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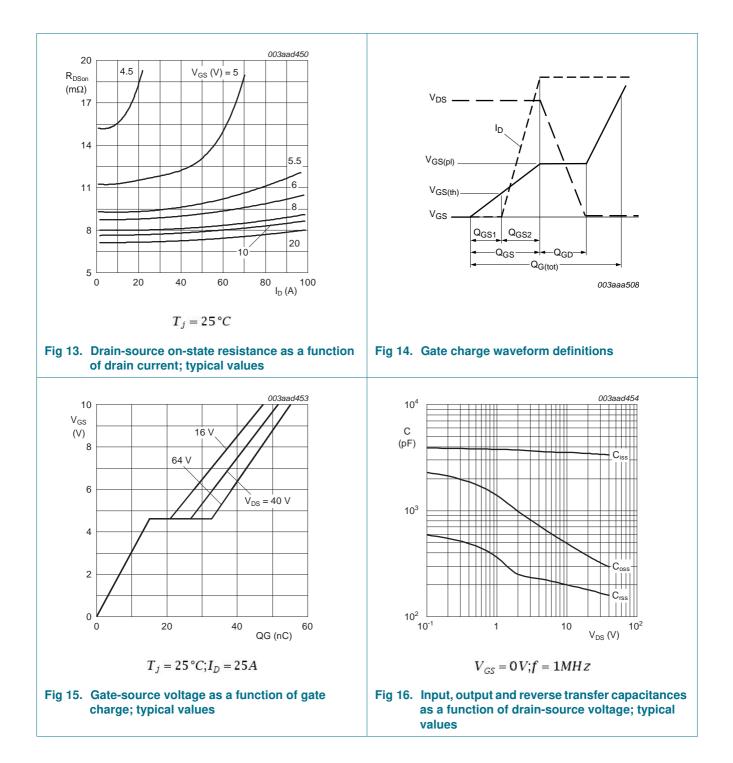
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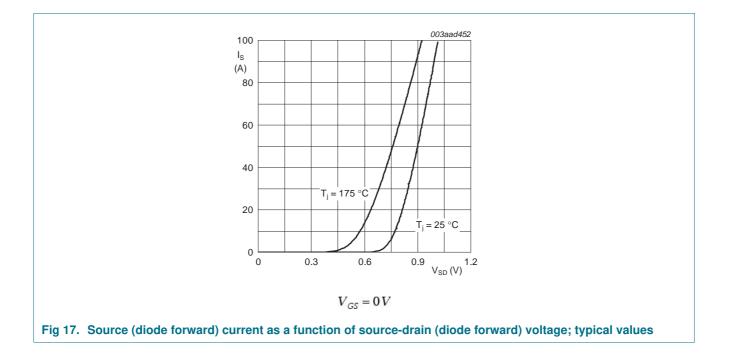
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7. Package outline

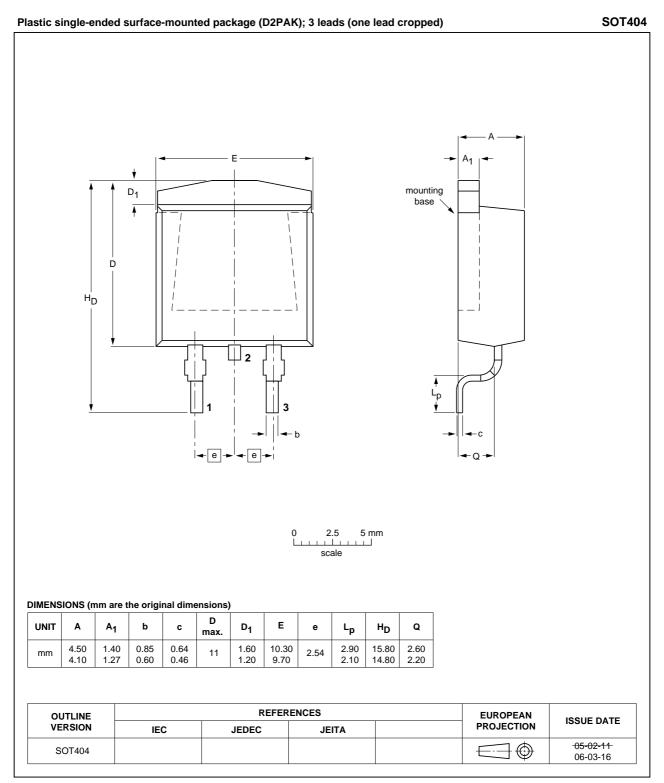


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R7-80BS v.2	20120302	Product data sheet	-	PSMN8R7-80BS v.1
Modifications:	Status changedVarious change	from objective to product. s to content.		
PSMN8R7-80BS v.1	20111024	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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